

74HC00; 74HCT00

Quad 2-input NAND gate

Rev. 04 — 11 January 2010

Product data sheet

1. General description

The 74HC00; 74HCT00 are high-speed Si-gate CMOS devices that comply with JEDEC standard no. 7A. They are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC00; 74HCT00 provides a quad 2-input NAND function.

2. Features

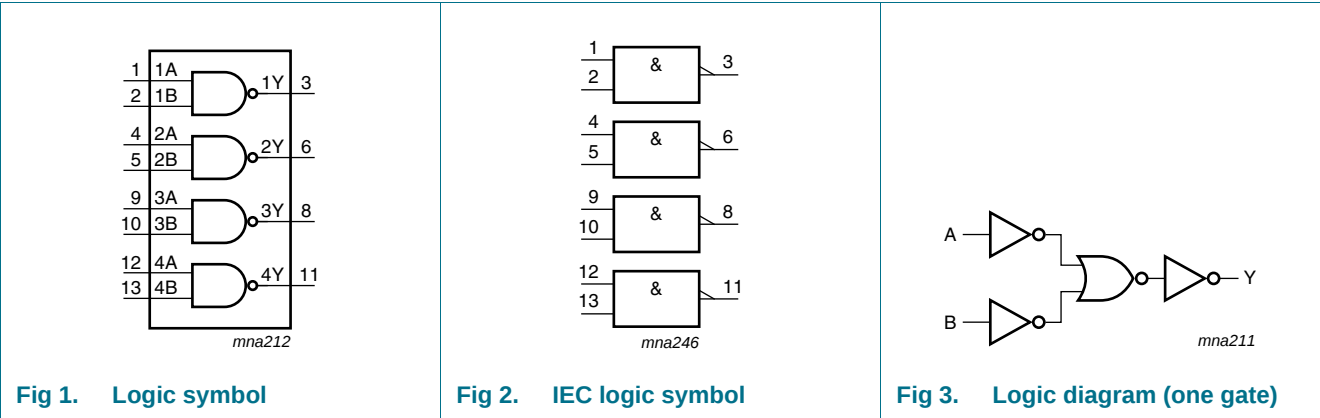
- Input levels:
 - ◆ For 74HC00: CMOS level
 - ◆ For 74HCT00: TTL level
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40°C to $+85^{\circ}\text{C}$ and from -40°C to $+125^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

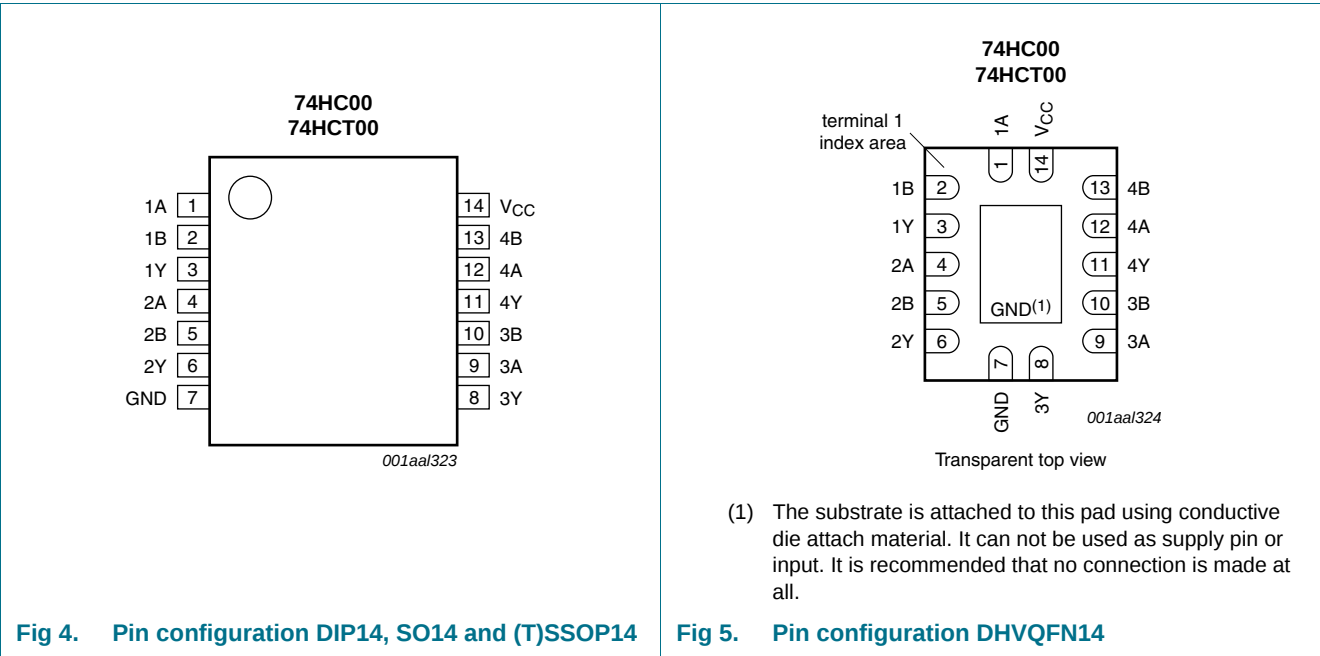
Type number	Package			
	Temperature range	Name	Description	Version
74HC00N 74HCT00N	-40°C to $+125^{\circ}\text{C}$	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
74HC00D 74HCT00D	-40°C to $+125^{\circ}\text{C}$	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74HC00DB 74HCT00DB	-40°C to $+125^{\circ}\text{C}$	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1
74HC00PW 74HCT00PW	-40°C to $+125^{\circ}\text{C}$	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74HC00BQ 74HCT00BQ	-40°C to $+125^{\circ}\text{C}$	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm	SOT762-1

4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A to 4A	1, 4, 9, 12	data input
1B to 4B	2, 5, 10, 13	data input
1Y to 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table^[1]

Input		Output
nA	nB	nY
L	X	H
X	L	H
H	H	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	^[1] -	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	^[1] -	±20	mA
I _O	output current	-0.5 V < V _O < V _{CC} + 0.5 V	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation		^[2]		
	DIP14 package		-	750	mW
	SO14, (T)SSOP14 and DHVQFN14 packages		-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For DIP14 package: P_{tot} derates linearly with 12 mW/K above 70 °C.
 For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 °C.
 For (T)SSOP14 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.
 For DHVQFN14 packages: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC00			74HCT00			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C

Table 5. Recommended operating conditions ...continued

Voltages are referenced to GND (ground = 0 V) ...continued

Symbol	Parameter	Conditions	74HC00			74HCT00			Unit
			Min	Typ	Max	Min	Typ	Max	
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5\text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC00										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	-	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	-	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	-	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	-	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	-	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	-	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = −20 μA; V _{CC} = 2.0 V	-	2.0	-	1.9	-	1.9	-	V
		I _O = −20 μA; V _{CC} = 4.5 V	-	4.5	-	4.4	-	4.4	-	V
		I _O = −20 μA; V _{CC} = 6.0 V	-	6.0	-	5.9	-	5.9	-	V
		I _O = −4.0 mA; V _{CC} = 4.5 V	-	4.32	-	3.84	-	3.7	-	V
		I _O = −5.2 mA; V _{CC} = 6.0 V	-	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	-	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	-	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	-	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	-	-	0.33	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	-	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	-	-	±1	-	±1	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	-	-	20	-	40	μA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT00										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	-	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = –20 μA	-	4.5	-	4.4	-	4.4	-	V
		I _O = –4.0 mA	-	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	-	-	0.1	-	0.1	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.15	-	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	-	-	±1	-	±1	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	-	-	20	-	40	μA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} – 2.1 V; I _O = 0 A; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V	-	150	-	-	675	-	735	μA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristicsGND = 0 V; C_L = 50 pF; for load circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +125 °C		Unit
			Min	Typ	Max	Max (85 °C)	Max (125 °C)	
74HC00								
t _{pd}	propagation delay	nA, nB to nY; see Figure 6	[1]					
		V _{CC} = 2.0 V	-	25	-	115	135	ns
		V _{CC} = 4.5 V	-	9	-	23	27	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	7	-	-	-	ns
		V _{CC} = 6.0 V	-	7	-	20	23	ns
t _t	transition time	see Figure 6	[2]					
		V _{CC} = 2.0 V	-	19	-	95	110	ns
		V _{CC} = 4.5 V	-	7	-	19	22	ns
		V _{CC} = 6.0 V	-	6	-	16	19	ns
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC}	[3]	-	22	-	-	pF

Table 7. Dynamic characteristics
GND = 0 V; C_L = 50 pF; for load circuit see Figure 7.

Symbol	Parameter	Conditions	25 °C			−40 °C to +125 °C		Unit	
			Min	Typ	Max	Max (85 °C)	Max (125 °C)		
74HCT00									
t _{pd}	propagation delay	nA, nB to nY; see Figure 6	[1]						
		V _{CC} = 4.5 V	-	12	-	24	29	ns	
		V _{CC} = 5.0 V; C _L = 15 pF	-	10	-	-	-	ns	
t _t	transition time	V _{CC} = 4.5 V; see Figure 6	[2]	-	-	-	29	22	ns
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} − 1.5 V	[3]	-	22	-	-	-	pF

- [1] t_{pd} is the same as t_{PHL} and t_{PLH}.
- [2] t_t is the same as t_{THL} and t_{TLH}.
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):
P_D = C_{PD} × V_{CC}² × f_i × N + Σ (C_L × V_{CC}² × f_o) where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
Σ (C_L × V_{CC}² × f_o) = sum of outputs.

11. Waveforms

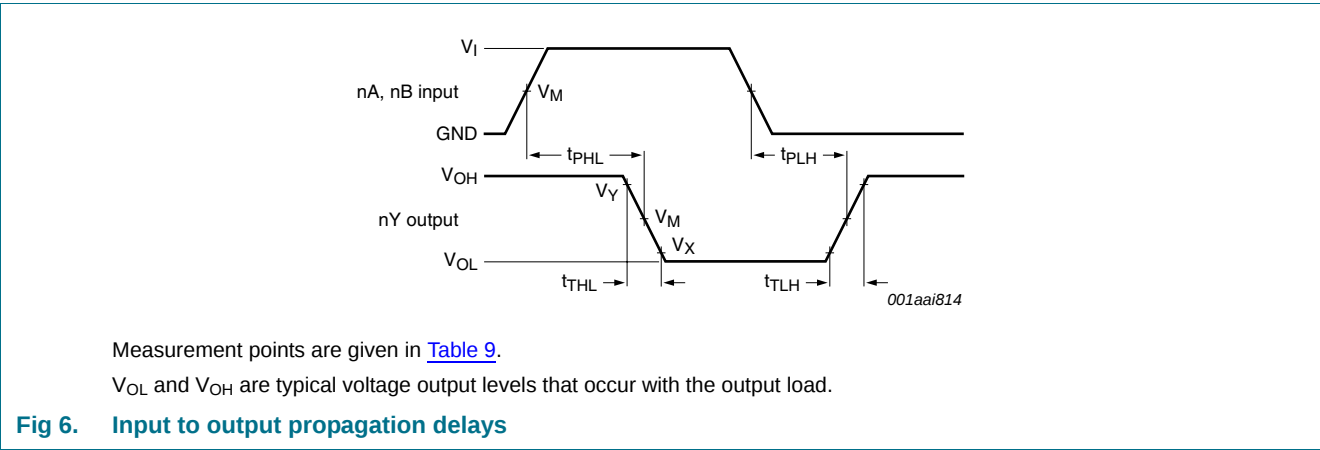
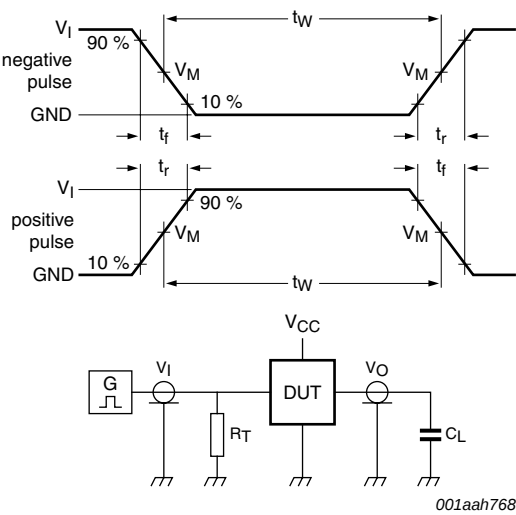


Table 8. Measurement points

Type	Input	Output		
	V _M	V _M	V _X	V _Y
74HC00	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}
74HCT00	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}



Test data is given in [Table 9](#).
Definitions test circuit:
 R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.
 C_L = load capacitance including jig and probe capacitance.

Fig 7. Load circuitry for measuring switching times

Table 9. Test data

Type	Input		Load	Test
	V_I	t_r, t_f	C_L	
74HC00	V_{CC}	6.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}
74HCT00	3.0 V	6.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}

12. Package outline

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1

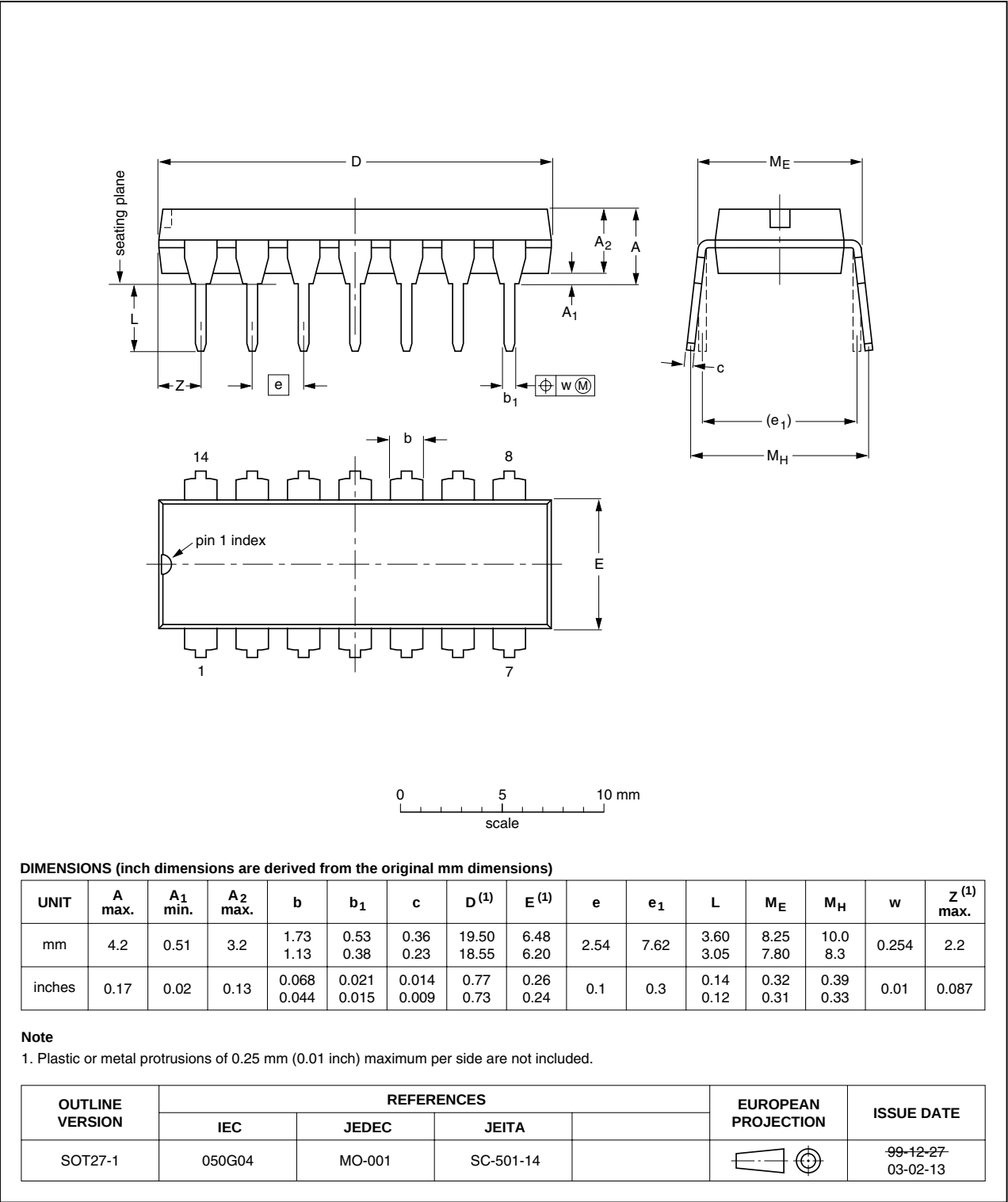


Fig 8. Package outline SOT27-1 (DIP14)

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

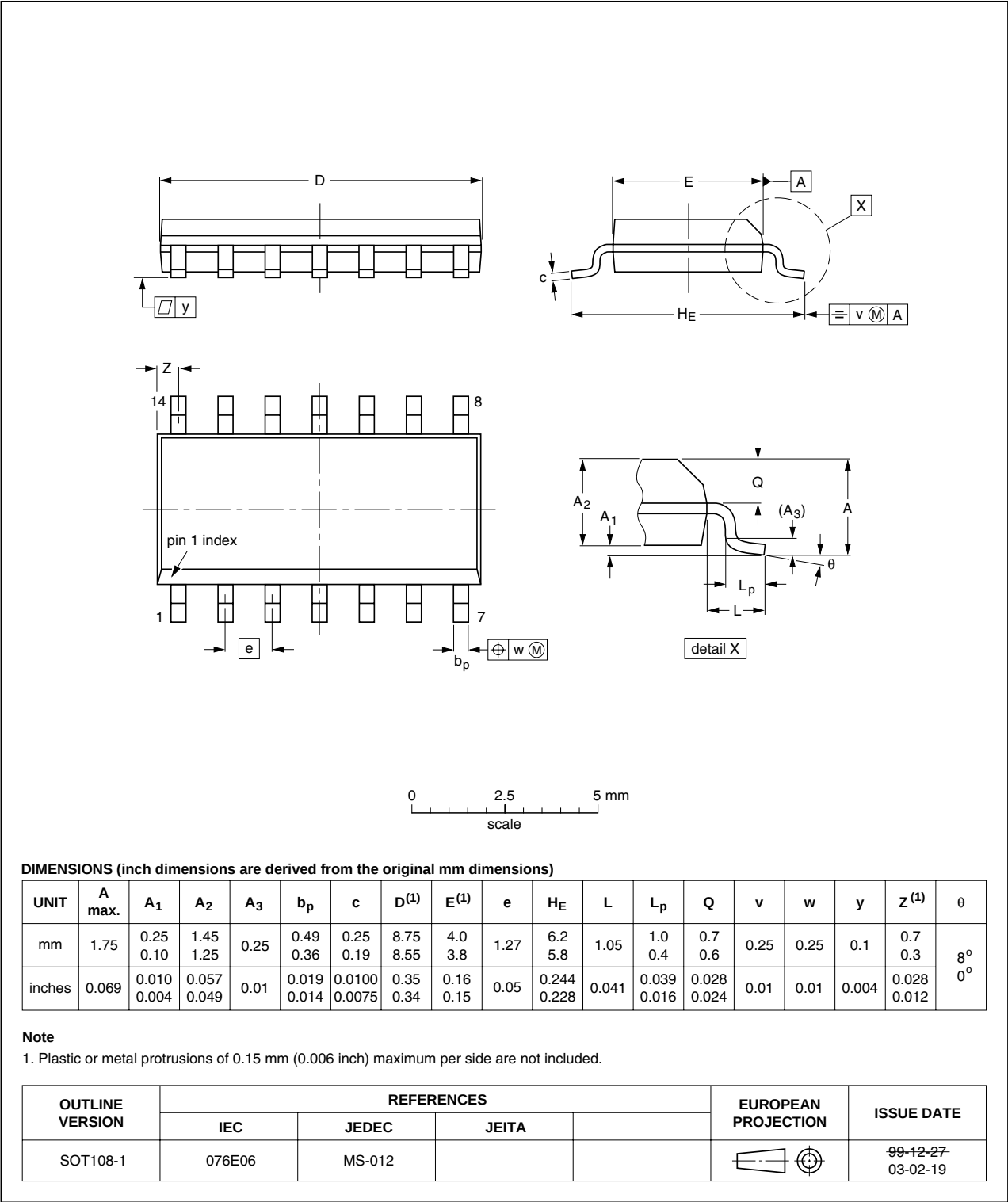


Fig 9. Package outline SOT108-1 (SO14)

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1

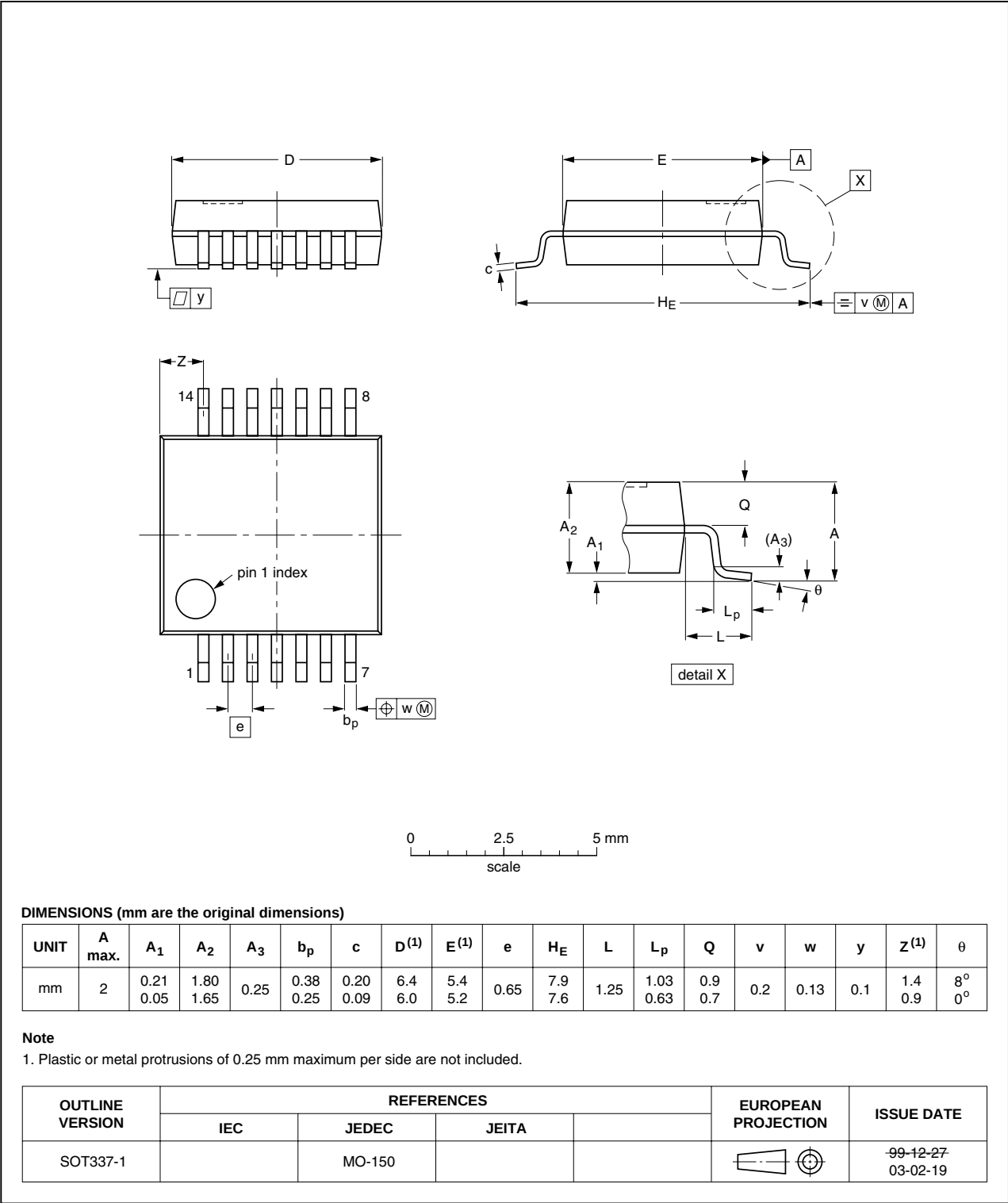


Fig 10. Package outline SOT337-1 (SSOP14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

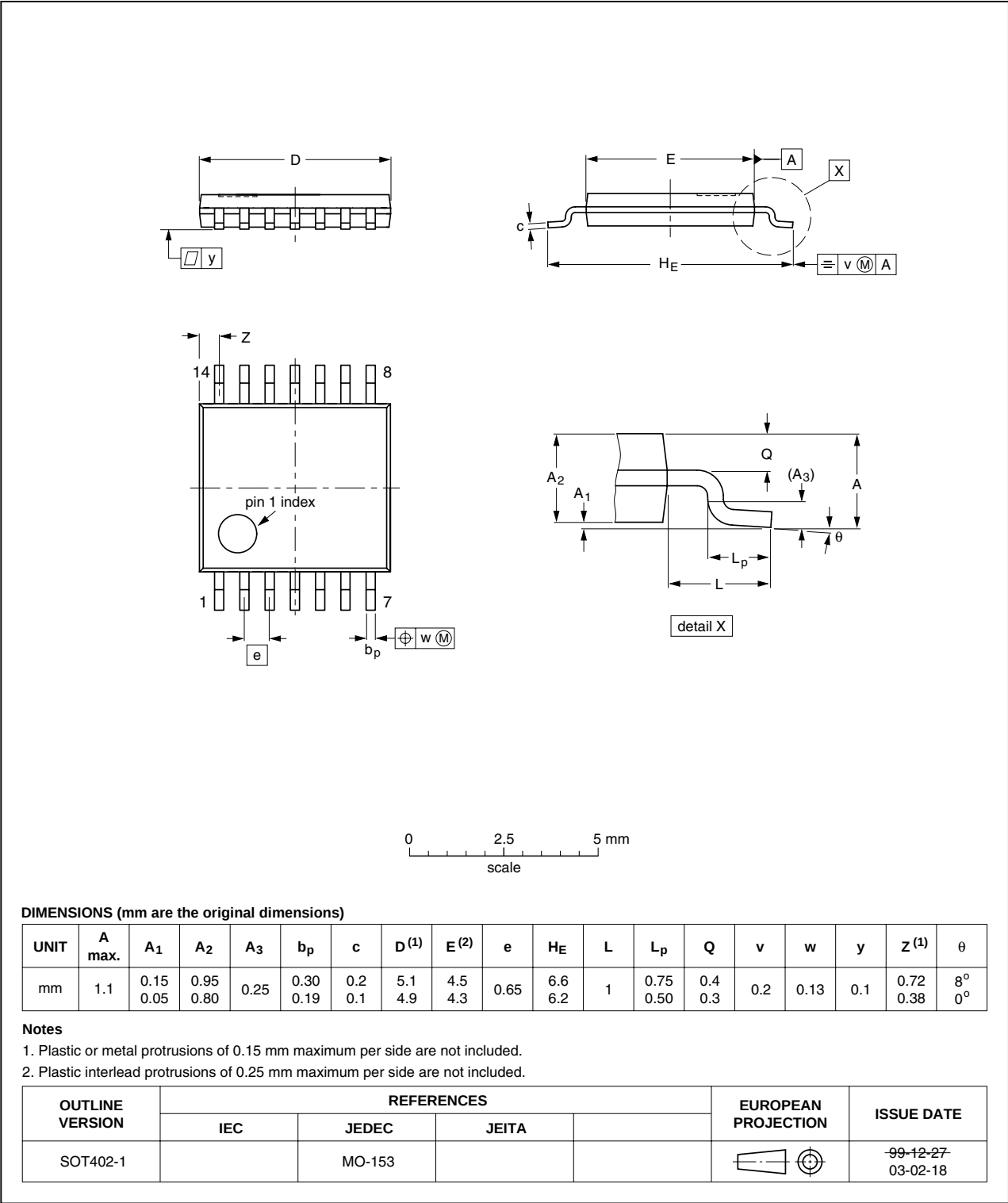


Fig 11. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;
14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1

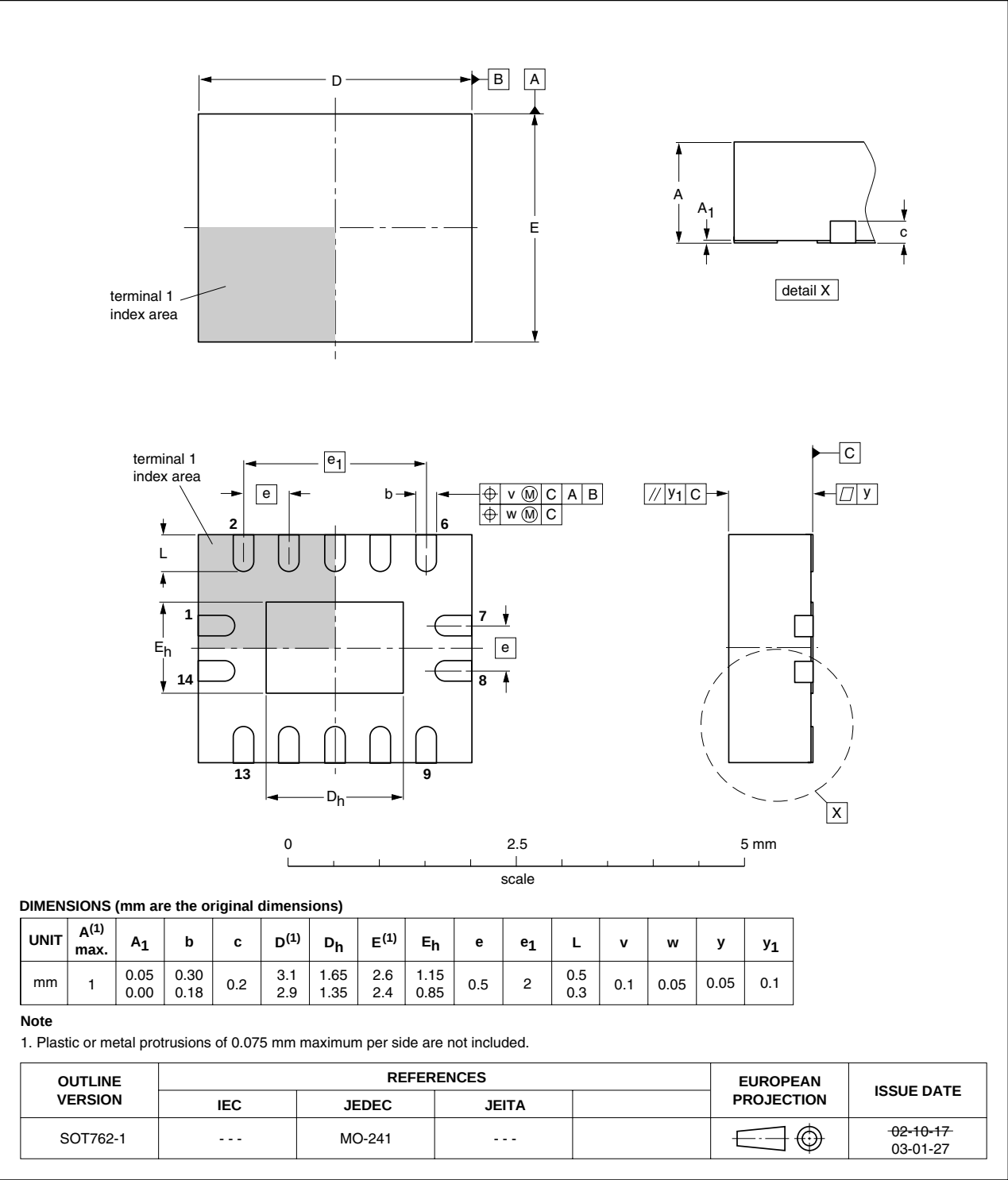


Fig 12. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT00_4	20100111	Product data sheet	-	74HC_HCT00_3
Modifications:	- The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. - Legal texts have been adapted to the new company name where appropriate.			
74HC_HCT00_3	20030630	Product data sheet	-	74HC_HCT00_CNV_2
74HC_HCT00_CNV_2	19970826	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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